

Memory materials and devices: From concept to applica

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Recent advances, perspectives, and challenges in ferroelectric synapses*. Chinese Physics B, 2020, 29, 097701.	1.4	19
2	Stimuli-Enabled Artificial Synapses for Neuromorphic Perception: Progress and Perspectives. Small, 2020, 16, e2001504.	10.0	55
3	Silent Synapse Activation by Plasma-Induced Oxygen Vacancies in TiO ₂ Nanowire-Based Memristor. Advanced Electronic Materials, 2020, 6, 2000536.	5.1	17
4	Unveiling the structural origin to control resistance drift in phase-change memory materials. Materials Today, 2020, 41, 156-176.	14.2	96
5	Recent Progress on Memristive Convolutional Neural Networks for Edge Intelligence. Advanced Intelligent Systems, 2020, 2, 2000114.	6.1	19
6	Recent Progress in Optoelectronic Synapses for Artificial Visual Perception System. Small Structures, 2020, 1, 2000029.	12.0	90
7	Flexible full two-dimensional memristive synapses of graphene/WS ₂ /xO _y /graphene. Physical Chemistry Chemical Physics, 2020, 22, 20658-20664.	2.8	16
8	The incorporation of the ionization effect in organic semiconductors assists in triggering multilevel resistive memory behaviors. Materials Chemistry Frontiers, 2020, 4, 3280-3289.	5.9	13
9	Non-volatile programmable homogeneous lateral MoTe ₂ junction for multi-bit flash memory and high-performance optoelectronics. Nano Research, 2020, 13, 3445-3451.	10.4	11
10	Self-Selective Resistive Device With Hybrid Switching Mode for Passive Crossbar Memory Application. IEEE Electron Device Letters, 2020, 41, 1009-1012.	3.9	34
11	High-Performance Broadband Tungsten Disulfide Photodetector Decorated with Indium Arsenide Nanoislands. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000297.	1.8	2
12	Improving the Recognition Accuracy of Memristive Neural Networks via Homogenized Analog Type Conductance Quantization. Micromachines, 2020, 11, 427.	2.9	8
13	Flexible 3D memristor array for binary storage and multi-states neuromorphic computing applications. Information Materials, 2021, 3, 212-221.	17.3	52
14	Recent progresses of NMOS and CMOS logic functions based on two-dimensional semiconductors. Nano Research, 2021, 14, 1768-1783.	10.4	19
15	Electronics based on two-dimensional materials: Status and outlook. Nano Research, 2021, 14, 1752-1767.	10.4	59
16	Ambipolar 2D Semiconductors and Emerging Device Applications. Small Methods, 2021, 5, e2000837.	8.6	39
17	2D Polarized Materials: Ferromagnetic, Ferrovalley, Ferroelectric Materials, and Related Heterostructures. Advanced Materials, 2021, 33, e2004469.	21.0	45
18	Enhancing light-matter interaction in 2D materials by optical micro/nano architectures for high-performance optoelectronic devices. Information Materials, 2021, 3, 36-60.	17.3	59

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19	Memristive Switching Characteristics in Biomaterial Chitosan-Based Solid Polymer Electrolyte for Artificial Synapse. International Journal of Molecular Sciences, 2021, 22, 773.	4.1	25
20	Nonlinear Weight Quantification for Mitigating Stress Induced Disturb Effect on Multilevel RRAM-Based Neural Network Accelerator. IEEE Journal of the Electron Devices Society, 2021, , 1-1.	2.1	1
21	A wafer-scale synthesis of monolayer MoS ₂ and their field-effect transistors toward practical applications. Nanoscale Advances, 2021, 3, 2117-2138.	4.6	31
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23	Emulation of biphasic plasticity in retinal electrical synapses for light-adaptive pattern pre-processing. Nanoscale, 2021, 13, 3483-3492.	5.6	16
24	High-performance flexible resistive random access memory devices based on graphene oxidized with a perpendicular oxidation gradient. Nanoscale, 2021, 13, 2448-2455.	5.6	12
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28	Change in Structure of Amorphous Sb ⁴⁺ Te Phase-Change Materials as a Function of Stoichiometry. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100064.	2.4	10
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57	Emulation of Synaptic Scaling Based on MoS ₂ Neuristor for Selfâ€Adaptative Neuromorphic Computing. <i>Advanced Electronic Materials</i> , 2021, 7, 2001104.	5.1	3
58	Design and tailoring of two-dimensional Schottky, PN and tunnelling junctions for electronics and optoelectronics. <i>Nanoscale</i> , 2021, 13, 6713-6751.	5.6	30
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67	Modulation of oxygen transport by incorporating Sb ₂ Te ₃ layer in HfO ₂ -based memristor. <i>Applied Physics Letters</i> , 2021, 119, 193503.	3.3	2
68	Single Crystal Halide Perovskite Film for Nonlinear Resistive Memory with Ultrahigh Switching Ratio. <i>Small</i> , 2022, 18, e2103881.	10.0	13
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75	Two-dimensional reconfigurable electronics enabled by asymmetric floating gate. <i>Nano Research</i> , 2022, 15, 4439-4447.	10.4	6
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